commodore mos technology NMOS

950 Rittenhouse Rd., Norristown, PA 19403 • Tel.: 215/666-7950 • TWX: 510/660-4168

6510 MICROPROCESSOR WITH I/O

DESCRIPTION

The 6510 is a low-cost microcomputer system capable of solving a broad range of small-systems and peripheral-control problems at minimum cost to the user.

An 8-bit Bi-Directional I/O Port is located on-chip with the Output Register at Address 0001 and the Data-Direction Register at Address 0000. The I/O Port is bit-by-bit programmable.

The Three-State sixteen-bit Address Bus allows Direct Memory Accessing (DMA) and multiprocessor systems sharing a common memory.

The internal processor architecture is identical to the MQS Technology 6502 to provide software compatibility.

FEATURES OF THE 6510.

- 8-Bit Bi-Directional I/O Port
- 256 Bytes fully Static RAM (internal)
- Single +5 volt supply
- N channel, silicon gate, depletion load technology
- Eight bit parallel processing
- 56 Instructions
- Decimal and binary arithmetic
- Thirteen addressing modes .
- True indexing capability .
- Programmable stack pointer .
- Variable length stack
- Interrupt capability .
- 8 Bit Bi-Directional Data Bus .
- Addressable memory range of up to 65K bytes .
- Direct memory access capability . .
- Bus compatible with M6800 **Pipeline architecture**
- 1 MHz and 2MHz operation
- Use with any type or speed memory

PIN CONFIGURATION

RES	1		40	Ø2 IN
Ø1 IN	2		39	R/W
IRQ	3		38	DB₀
AEC	4		37	DB,
VCC	5		36	DB2
A	6		35	DB,
Α,	7		34	DB.
A ₂	8		33	DB
Α,	9		32	DB₀
A₄	10	6510	31	DB,
A ₅	11		30	P。
As	12		29	Ρ,
Α,	13		28	P ₂
A ₈	14		27	P ₃
Α,	15		26	P₄
A10	16		25	P _s
Α,,	17		24	P ₆
A,,	18		23	Ρ,
A ₁₃	19		22	A, 5
VSS	20		21	A.,



6510 CHARACTERISTICS

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
SUPPLY VOLTAGE	Vcc	-0.3 to +7.0	Vdc
INPUT VOLTAGE	Vin	-0.3 to +7.0	Vdc
OPERATING TEMPERATURE	TA	0 to +70	°C
STORAGE TEMPERATURE	TSTG	- 55 to + 150	°C

This device contains input protection against damage due to high static voltages or electric fields; however, precautions should be taken to avoid application of voltages higher than the maximum rating.

ELECTRICAL CHARACTERISTICS (Vcc = $5.0V \pm 5\%$, Vss = 0, T_A = 0° to + 70°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Input High Voltage					
Ø1, Ø2(in)	VIH	Vcc - 0.2	,—	Vcc + 1.0V	Vdc
Input High Voltage			1		
RES, P₀-P,IRQ, Data		Vss + 2.0	_	_	Vdc
nput Low Voltage					
Ø1, Ø2(in)	VIL	Vss - 0.3	-	Vss + 0.2	Vdc
RES, P ₀ -P, IRQ, Data		-		Vss + 0.8	Vdc
Input Leakage Current					
(V _{in} = 0 to 5.25V, Vcc = 5.25V) Logic	lin	_	_	2.5	μΑ
Ø ₁ , Ø ₂ (in)		-	-	100	μΑ
Three State (Off State) Input Current					
$(V_{in} = 0.4 \text{ to } 2.4\text{V}, \text{Vcc} = 5.25\text{V})$					
Data Lines	ITSI			10	μΑ
Output High Voltage				-	
$(I_{OH} = -100\mu Adc, Vcc = 4.75V)$ Data, AO-A15, R/W, P ₀ -P ₇	VOH	Vss + 2.4		_	Vdc
Out Low Voltage					
$(I_{OL} = 1.6 \text{mAdc}, \text{Vcc} = 4.75 \text{V})$					
Data, A0-A15, R/W, P ₀ -P ₇	VOL		-	Vss + 0.4	Vdc
Power Supply Current	ICC	_	125		mA
Capacitance	С				pF
$V_{in} = O, T_A = 25^{\circ}C, f = 1MHz$					
Logic, P ₀ -P ₇	C _{in}	-	-	10	
Data		-	_	15	
AO-A15, R/W	Cout	-		12	
Ø,	C _Ø ,	-	30	50	
Ø,	C _{Ø2}	-	50	80	





AC CHARACTERISTICS

1 MHz TIMING

2 MHz TIMING

ELECTRICAL CHARACTERISTICS (VCC = 5V \pm 5%, VSS = 0V, T_A = 0° -70°C)

CLOCK TIMING

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS
Cycle Time	TCYC	1000	-	· <u></u>	500		-	ns
Clock Pulse Width Ø1 (Measured at VCC - 0.2V) Ø2	PWHØ1 PWHØ2	430 470	-	_	215 235	_	=	ns ns
Fall Time, Rise Time (Measured from 0.2V to VCC-0.2V)	T _F , T _R		—	25		_	15	ns
Delay Time between Clocks (Measured at 0.2V)	Тр	0	-	_	0	_	_	ns

READ/WRITE TIMING (LOAD=1TTL)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	UNITS
Read/Write Setup Time from 6508	TRWS	-	100	300	—	100	150	ns
Address Setup Time from 6508	TADS	-	100	300	_	100	150	ns
Memory Read Access Time	TACC		-	575	-	-	300	ns
Data Stability Time Period	TDSU	100		-	50			ns
Data Hold Time-Read	THR	10	—	-	10			ns
Data Hold Time-Write	THW	10	30		10	30		ns
Data Setup Time from 6510	T _{MDS}	-	150	200	—	75	100	ns
Address Hold Time	T _{HA}	10	30	~	10	30		ns
R/W Hold Time	THRW	10	30	~	10	30		ns
Delay Time, Ø2 negative transition			1. 1. 191 1910 - 9 1					
to Peripheral Data valid	TPDW	_	<u> </u>	300			150	μs
Peripheral Data Setup Time	TPDSU	300	—	~	150			ns
Address Enable Setup Time	TAES			75			75	ns
Address Disable *See Note 1	TAED			120			120	ns
Data Enable Setup Time	TDES			120			120	ns
Data Disable *See Note 1	TDED			130			130	ns

*Note 1 - 1TTL Load

CL = 30 pf

SIGNAL DESCRIPTION

Clocks $(\emptyset_1, \emptyset_2)$

The 6510 requires a two phase non-overlapping clock that runs at the Vcc voltage level.

Address Bus (A₀·A₁₅)

The tri state outputs are TTL compatible, capable of driving one standard TTL load and 130 pf.

Data Bus (D₀-D₇)

Eight pins are used for the data bus. This is a Bi-Directional bus, transferring data to and from the device and peripherals. The outputs are tri-state buffers capable of driving one standard TTL load and 130 pf.

Reset

This input is used to reset or start the microprocessor from a power down condition. During the time that this line is held low, writing to or from the microprocessor is inhibited. When a positive edge is detected on the input, the microprocessor will immediately begin the reset sequence.

After a system initialization time of six clock cycles, the mask interrupt flag will be set and the microprocessor will load the program counter from the memory vector locations FFFC and FFFD. This is the start location for program control.

After Vcc reaches 4.75 volts in a power up routine, reset must be held low for at least two clock cycles. At this time the R/W signal will become valid.

When the reset signal goes high following these two clock cycles, the microprocessor will proceed with the normal reset procedure detailed above.

Interrupt Request (IRQ)

This TTL level input requests that an interrupt sequence begin within the microprocessor. The microprocessor will complete the current instruction being executed before recognizing the request. At that time, the interrupt mask bit in the Status Code Register will be examined. If the interrupt mask flag is not set, the microprocessor will begin an interrupt sequence. The Program Counter and Processor Status Register are stored in the stack. The microprocessor will then set the interrupt mask flag high so that no further interrupts may occur. At the end of this cycle, the program counter low will be loaded from address FFFE, and program counter high from location FFFF, therefore transferring program control to the memory vector located at these addresses.

Address Enable Control (AEC)

The Address Bus is valid only when the Address Enable Control line is high. When low, the Address Bus is in a high-impedance state. This feature allows easy DMA and multiprocessor systems.

I/O Port (P₀-P₇)

Eight pins are used for the peripheral port, which can transfer data to or from peripheral devices. The Output Register is located in RAM at Address 0001, and the Data Direction Register is at Address 0000. The outputs are capable at driving one standard TTL load and 130 pf.

Read/Write (R/W)

This signal is generated by the microprocessor to control the direction of data transfers on the Data Bus. This line is high except when the microprocessor is writing to memory or a peripheral device.

ACCUMULATOR ADDRESSING—This form of addressing is represented with a one byte instruction, implying an operation on the accumulator.

IMMEDIATE ADDRESSING—In immediate addressing, the operand is contained in the second byte of the instruction, with no further memory addressing required.

ABSOLUTE ADDRESSING—In absolute addressing, the second byte of the instruction specifies the eight low order bits of the effective address while the third byte specifies the eight high order bits. Thus, the absolute addressing mode allows access to the entire 65K bytes of addressable memory.

ZERO PAGE ADDRESSING—The zero page instructions allow for shorter code and execution times by only fetching the second byte of the instruction and assuming a zero high address byte. Careful use of the zero page can result in significant increase in code efficiency.

INDEXED ZERO PAGE ADDRESSING—(X, Y indexing)—This form of addressing is used in conjunction with the index register and is referred to as "Zero Page, X" or "Zero Page, Y." The effective address is calculated by adding the second byte to the contents of the index register. Since this is a form of "Zero Page" addressing, the content of the second byte references a location in page zero. Additionally, due to the "Zero Page" addressing nature of this mode, no carry is added to the high order 8 bits of memory and crossing of page boundaries does not occur.

INDEXED ABSOLUTE ADDRESSING—(X, Y indexing)—This form of addressing is used in conjunction with X and Y index register and is referred to as "Absolute, X," and "Absolute, Y." The effective address is formed by adding the contents of X and Y to the address contained in the second and third bytes of the instruction. This mode allows the index register to contain the index or count value and the instruction to contain the base address. This type of indexing allows any location referencing and the index to modify multiple fields resulting in reduced coding and execution time.

IMPLIED ADDRESSING—In the implied addressing mode, the address containing the operand is implicitly stated in the operation code of the instruction.

RELATIVE ADDRESSING—Relative addressing is used only with branch instructions and establishes a destination for the conditional branch.

The second byte of the instruction becomes the operand which is an "Offset" added to the contents of the lower eight bits of the program counter when the counter is set at the next instruction. The range of the offset is -128 to +127 bytes from the next instruction.

INDEXED INDIRECT ADDRESSING—In indexed indirect addressing (referred to as [Indirect, X]), the second byte of the instruction is added to the contents of the X index register, discarding the carry. The result of this addition points to a memory location on page zero whose contents is the low order eight bits of the effective address. The next memory location in page zero contains the high order eight bits of the effective address. Both memory locations specifying the high and low order bytes of the effective address must be in page zero.

INDIRECT INDEXED ADDRESSING—In indirect indexed addressing (referred to as [Indirect, Y]). the second byte of the instruction points to a memory location in page zero. The contents of this memory location is added to the contents of the Y index register, the result being the low order eight bits of the effective address. The carry from this addition is added to the contents of the next page zero memory location, the result being the high order eight bits of the effective address.

ABSOLUTE INDIRECT—The second byte of the instruction contains the low order eight bits of a memory location. The high order eight bits of that memory location is contained in the third byte of the instruction. The contents of the fully specified memory location is the low order byte of the effective address. The next memory location contains the high order byte of the effective address which is loaded into the sixteen bits of the program counter.

ADC	Add Memory to Accumulator with Carry	LDA	Load Accumulator with Memory
AND	"AND" Memory with Accumulator	LDX	Load Index X with Memory
ASL	Shift left One Bit (Memory or Accumulator)	LDY	Load Index Y with Memory
BCC	Branch on Carry Clear	LSR	Shift One Bit Right (Memory or Accumulator)
BCS	Branch on Carry Set	NOP	No Operation
BEQ BIT BMI	Branch on Result Zero Test Bits in Memory with Accumulator Branch on Result Minus	ORA	"OR" Memory with Accumulator
BNE BPL BRK BVC BVS	Branch on Result not Zero Branch on Result Plus Force Break Branch on Overflow Clear Branch on Overflow Set	PHA PHP PLA PLP	Push Accumulator on Stack Push Processor Status on Stack Pull Accumulator from Stack Pull-Processor Status from Stack
CLC	Clear Carry Flag	ROL	Rotate One Bit Left (Memory or Accumulator)
CLD	Clear Decimal Mode	ROR	Rotate One Bit Right (Memory or Accumulator)
CLI	Clear interrupt Disable Bit	RTI	Return from Interrupt
CLV	Clear Overflow Flag	RTS	Return from Subroutine
CMP	Compare Memory and Accumulator	SBC	Subtract Memory from Accumulator with Borrow
CPX	Compare Memory and Index X	SEC	Set Carry Flag
CPY	Compare Memory and Index Y	SED	Set Decimal Mode
DEC DEX DEY	Decrement Memory by One Decrement Index X by One Decrement Index Y by One	SEI STA STX STY	Set Interrupt Disable Status Store Accumulator in Memory Store Index X in Memory Store Index Y in Memory
EOR	"Exclusive-or" Memory with Accumulator	TAX	Transfer Accumulator to Index X
INC	Increment Memory by One	TAY	Transfer Accumulator to Index Y
INX	Increment Index X by One	TSX	Transfer Stack Pointer to Index X
INY	Increment Index Y by One	TXA	Transfer Index X to Accumulator
JMP	Jump to New Location	TXS	Transfer Index X to Stack Register
JSR	Jump to New Location Saving Return Address	TYA	Transfer Index Y to Accumulator

INSTRUCTION SET—ALPHABETIC SEQUENCE



INSTRUCTION SET – OP CODES, Execution Time, Memory Requirements

	STRUCTIONS	-	DIAT			LUTE		EROP	AGE		CCU			LIED	_	(IND			ND).Y		J.PAG			88,X	_	A85.1			ATIVE			RECT			GE.	- 1				CODE	-
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Note: Commodore Semiconductor Group cannot assume liability for the use of undefined OP Codes



6510 MEMORY MAP

APPLICATIONS NOTES

Locating the Output Register at the internal I/O Port in Page Zero enhances the powerful Zero Page Addressing instructions of the 6510.

By assigning the I/O Pins as inputs (using the Data Direction Register) the user has the ability to change the contents of address 0001 (the Output Register) using peripheral devices. The ability to change these contents using peripheral inputs, together with Zero Page Indirect Addressing instructions, allows novel and versatile programming techniques not possible earlier.

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